



## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:

YOSHIDA, et al

Serial No.:

10/042,271

Filed:

January 11, 2002

For:

ABRASIVE METHOD OF POLISHING TARGET MEMBER AND

PROCESS FOR PRODUCING SEMICONDUCTOR DEVICE

Group (anticipated): 3723

Examiner (anticipated): D. Nguyen

## SUPPLEMENTAL PRELIMINARY AMENDMENT

Assistant Commissioner of Patents Washington, D.C. 20231

January 25, 2002

Sir:

Supplemental to the Preliminary Amendment filed on January 11, 2002, please amend the application as follows:

RECEIVED

IN THE CLAIMS

JUN 0 7 2004

Please cancel Claims 1, 26 and 29.

**TECHNOLOGY CENTER R370**0

Please add the following new Claims 30 - 49:

--30. An abrasive comprising cerium oxide particles, said particles having a crystal grain boundary and having a maximum